Motoaki Iwaya

List of Publications by Year
in descending order

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154	3,630	147801	168389
papers	citations	31	53
		h-index	g-index

155	155	155	2104
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Analysis of impurity doping in tunnel junction grown on coreâ€“shell structure composed of GaInN/GaN multiple-quantum-shells and GaN nanowire. Japanese Journal of Applied Physics, 2022, 61, 012002.	1.5	1
2	MOVPE growth of Si-doped GaN cap layers embedding GaN nanowires with multiple-quantum shells. Journal of Crystal Growth, 2022, 578, 126423.	1.5	2
3	Recent development of UV-B laser diodes. Japanese Journal of Applied Physics, 2022, 61, 040501.	1.5	13
4	Improved passivation depth of porous fluorescent 6H-SiC with Si/C faces using atomic layer deposition. Japanese Journal of Applied Physics, 2022, 61, 035502.	1.5	0
5	Reduction of dislocation density in lattice-relaxed Al_{0.68}Ga_{0.32}N film grown on periodical 1 Î¼m spacing AlN pillar concave-convex patterns and its effect on the performance of UV-B laser diodes. Applied Physics Express, 2022, 15, 031004.	2.4	16
6	Fabrication of vertical AlGaN-based deep-ultraviolet light-emitting diodes operating at high current density (âˆ¼43 kA cm^{â^'2}) using a laser liftoff method. Applied Physics Express, 2022, 15, 041006.	2.4	9
7	Centimeter-scale laser lift-off of an AlGaN UVB laser diode structure grown on nano-patterned AlN. Applied Physics Express, 2022, 15, 051004.	2.4	9
8	Improvement of 650-nm red-emitting GaIn0.17N/GaIn0.38N multiple quantum wells on ScAlMgO4 (0001) substrate by suppressing impurity diffusion/penetration. Applied Physics Letters, 2022, 120, .	3.3	12
9	Color-tunable emission in coaxial GaInN/GaN multiple quantum shells grown on three-dimensional nanostructures. Applied Surface Science, 2021, 539, 148279.	6.1	11
10	AlGaN-based UV-B laser diode with a high optical confinement factor. Applied Physics Letters, 2021, 118, .	3.3	36
11	Room temperature pulsed operation of nitride nanowire-based multi-quantum shell laser diodes by MOVPE. Applied Physics Express, 2021, 14, 074004.	2.4	6
12	Analysis of carrier injection efficiency of AlGaN UV-B laser diodes based on the relationship between threshold current density and cavity length. Japanese Journal of Applied Physics, 2021, 60, 074002.	1.5	10
13	Crystal Growth and Characterization of n-GaN in a Multiple Quantum Shell Nanowire-Based Light Emitter with a Tunnel Junction. ACS Applied Materials & Interfaces, 2021, 13, 37883-37892.	8.0	5
14	Space-charge effect on photogenerated-current and -voltage in III-nitride optoelectronic semiconductors. Photonics Research, 2021, 9, 1820.	7.0	2
15	Emission characteristics of GaInN/GaN multiple quantum shell nanowire-based LEDs with different p-GaN growth conditions. Nanophotonics, 2021, 10, 3441-3450.	6.0	8
16	Effects of Mg dopant in Al-composition-graded Al_xGa_{1â^'x}N (0.45Ââ‰Âx) on vertical electrical conductivity of ultrawide bandgap AlGaN pâ€“n junction. Applied Physics Express, 2021, 14, 096503.	2.4	8
17	Influence of silane flow rate on the structural and optical properties of GaN nanowires with multiple-quantum-shells. Journal of Crystal Growth, 2021, 570, 126201.	1.5	2
18	Low-threshold-current (~85 mA) of AlGaN-based UV-B laser diode with refractive-index waveguide structure. Applied Physics Express, 2021, 14, 094009.	2.4	14

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19	Reduction of dislocation density in Al0.6Ga0.4N film grown on sapphire substrates using annealed sputtered AlN templates and its effect on UV-B laser diodes. Journal of Crystal Growth, 2021, 575, 126325.	1.5	12
20	n-type GaN surface etched green light-emitting diode to reduce non-radiative recombination centers. Applied Physics Letters, 2021, 118, .	3.3	14
21	Identification of multi-color emission from coaxial GaInN/GaN multiple-quantum-shell nanowire LEDs. Nanoscale Advances, 2021, 4, 102-110.	4.6	14
22	Morphology Control and Crystalline Quality of p-Type GaN Shells Grown on Coaxial GaInN/GaN Multiple Quantum Shell Nanowires. ACS Applied Materials & Interfaces, 2021, 13, 54486-54496.	8.0	7
23	AlGaN-based UV-B laser diode fabricated on AlN with 1 Î¼m periodic concave and convex patterns. , 2021, , .		0
24	In-situ curvature measurements of AlInN/GaN distributed Bragg reflectors during growths containing substrate temperature ramping steps. Journal of Crystal Growth, 2020, 531, 125357.	1.5	2
25	Growth and Characterization of Core-Shell Structures Consisting of GaN Nanowire Core and GaInN/GaN Multi-Quantum Shell. ECS Journal of Solid State Science and Technology, 2020, 9, 015007.	1.8	21
26	Fabrication and Characterization of Multiquantum Shell Lightâ€Emitting Diodes with Tunnel Junction. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900774.	1.8	8
27	Efficiency Enhancement Mechanism of an Underlying Layer in GaInNâ€Based Green Lightâ€“Emitting Diodes. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900713.	1.8	7
28	Improved Uniform Current Injection into Coreâ€Shellâ€Type GaInN Nanowire Lightâ€Emitting Diodes by Optimizing Growth Condition and Indiumâ€Tinâ€Oxide Deposition. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900715.	1.8	15
29	Thermodynamic analysis of GaInN-based light-emitting diodes operated by quasi-resonant optical excitation. Journal of Applied Physics, 2020, 128, .	2.5	10
30	Development of Monolithically Grown Coaxial GaInN/GaN Multiple Quantum Shell Nanowires by MOCVD. Nanomaterials, 2020, 10, 1354.	4.1	13
31	Voltage-Controlled Anodic Oxidation of Porous Fluorescent SiC for Effective Surface Passivation. Nanomaterials, 2020, 10, 2075.	4.1	1
32	Correlation between Optical and Structural Characteristics in Coaxial GaInN/GaN Multiple Quantum Shell Nanowires with AlGaN Spacers. ACS Applied Materials & Interfaces, 2020, 12, 51082-51091.	8.0	10
33	Characterizations of GaN nanowires and GaInN/GaN multi-quantum shells grown by MOVPE. Japanese Journal of Applied Physics, 2020, 59, SGGE05.	1.5	5
34	Analysis of Spontaneous Subpeak Emission from the Guide Layers of the Ultravioletâ€B Laser Diode Structure Containing Compositionâ€Graded pâ€AlGaN Cladding Layers. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900864.	1.8	12
35	High Crystallinity and Highly Relaxed Al_{0.60}Ga_{0.40}N Films Using Growth Mode Control Fabricated on a Sputtered AlN Template with Highâ€Temperature Annealing. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900868.	1.8	16
36	Effects of Mg and Si doping in the guide layers of AlGaN-based ultraviolet-B band lasers. Journal of Crystal Growth, 2020, 535, 125537.	1.5	11

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37	Controlled synthesis of nonpolar GaInN/GaN multiple-quantum-shells on GaN nanowires by metal-organic chemical vapour deposition. Applied Surface Science, 2020, 509, 145271.	6.1	15
38	GaN-based vertical cavity surface emitting lasers with lateral optical confinements and conducting distributed Bragg reflectors. Japanese Journal of Applied Physics, 2020, 59, SGGE08.	1.5	12
39	MOVPE growth of n-GaN cap layer on GaInN/GaN multi-quantum shell LEDs. Journal of Crystal Growth, 2020, 539, 125571.	1.5	6
40	Structural and optical impacts of AlGaN undershells on coaxial GaInN/GaN multiple-quantum-shells nanowires. Nanophotonics, 2020, 9, 101-111.	6.0	10
41	Room-temperature continuous-wave operations of GaN-based vertical-cavity surface-emitting lasers with buried GaInN tunnel junctions. Applied Physics Express, 2020, 13, 111003.	2.4	12
42	High-quality AlInN/GaN distributed Bragg reflectors grown by metalorganic vapor phase epitaxy. Applied Physics Express, 2020, 13, 125504.	2.4	12
43	Cp₂Mg in-situ monitoring in a MOVPE reactor using a quantum cascade laser. Japanese Journal of Applied Physics, 2019, 58, SC1013.	1.5	0
44	Improvement of emission efficiency with a sputtered AlN buffer layer in GaInN-based green light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SC1040.	1.5	6
45	Electrical properties of relaxed p-GaN/p-AlGaN superlattices and their application in ultraviolet-B light-emitting devices. Japanese Journal of Applied Physics, 2019, 58, SC1016.	1.5	9
46	Influence of trap level on an Al0.6Ga0.4N/Al0.5Ga0.5N metalâ€”semiconductorâ€”metal UV photodetector. Japanese Journal of Applied Physics, 2019, 58, SCCC26.	1.5	2
47	Sapphire substrate off-angle and off-direction dependences on characteristics of AlGaN-based deep ultraviolet light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SC1025.	1.5	12
48	High photosensitivity AlGaN/GaInN/GaN heterojunction field-effect transistor type visible photosensors. Japanese Journal of Applied Physics, 2019, 58, SCCC22.	1.5	1
49	GaN-based vertical-cavity surface-emitting lasers using n-type conductive AlInN/GaN bottom distributed Bragg reflectors with graded interfaces. Japanese Journal of Applied Physics, 2019, 58, SCCC01.	1.5	15
50	450Ânm GaInN ridge stripe laser diodes with AlInN/AlGaN multiple cladding layers. Japanese Journal of Applied Physics, 2019, 58, SCCC28.	1.5	23
51	Modified Shockley Equation for GaInN-Based Light-Emitting Diodes: Origin of the Power- Efficiency Degradation Under High Current Injection. IEEE Journal of Quantum Electronics, 2019, 55, 1-11.	1.9	13
52	Optical and structural characterization of GaInN/GaN multiple quantum wells grown on nonpolar a-plane GaN templates by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2019, 58, SC1054.	1.5	1
53	The dependence of AlN molar fraction of AlGaN in wet etching by using tetramethylammonium hydroxide aqueous solution. Japanese Journal of Applied Physics, 2019, 58, SCCC30.	1.5	21
54	Hybrid simulation of light extraction efficiency in multi-quantum-shell (MQS) NW (nanowire) LED with a current diffusion layer. Japanese Journal of Applied Physics, 2019, 58, SCCC17.	1.5	14

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55	Ultraviolet-B band lasers fabricated on highly relaxed thick Al_{0.55}Ga_{0.45}N films grown on various types of AlN wafers. Japanese Journal of Applied Physics, 2019, 58, SC1052.	1.5	36
56	Optimization of indium tin oxide layer thickness for surface-plasmon-enhanced green light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SCCC27.	1.5	4
57	Light confinement and high current density in UVB laser diode structure using Al composition-graded p-AlGaN cladding layer. Applied Physics Letters, 2019, 114, .	3.3	33
58	Tuning the Resonant Frequency of a Surface Plasmon by Double-Metallic Ag/Au Nanoparticles for High-Efficiency Green Light-Emitting Diodes. Applied Sciences (Switzerland), 2019, 9, 305.	2.5	8
59	Determination of internal quantum efficiency in GaInN-based light-emitting diode under electrical injection: carrier recombination dynamics analysis. Applied Physics Express, 2019, 12, 032006.	2.4	21
60	Enhanced Device Performance of GaInN-Based Green Light-Emitting Diode with Sputtered AlN Buffer Layer. Applied Sciences (Switzerland), 2019, 9, 788.	2.5	10
61	Effect of AlGaN undershell on the cathodoluminescence properties of coaxial GaInN/GaN multiple-quantum-shells nanowires. Nanoscale, 2019, 11, 18746-18757.	5.6	23
62	Improved Reverse Leakage Current in GaInN-Based LEDs With a Sputtered AlN Buffer Layer. IEEE Photonics Technology Letters, 2019, 31, 1971-1974.	2.5	2
63	Characterization of nonpolar a-plane GaN epi-layers grown on high-density patterned r-plane sapphire substrates. Journal of Crystal Growth, 2018, 484, 50-55.	1.5	11
64	Growth of Highâ€Quality AlN and AlGaN Films on Sputtered AlN/Sapphire Templates via Highâ€Temperature Annealing. Physica Status Solidi (B): Basic Research, 2018, 255, 1700506.	1.5	30
65	High quality Al_{0.99}Ga_{0.01}N layers on sapphire substrates grown at 1150 Â°C by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2017, 56, 015504.	1.5	6
66	Characterization and optimization of sputtered AlN buffer layer on r-plane sapphire substrate to improve the crystalline quality of nonpolar a-plane GaN. Journal of Crystal Growth, 2017, 480, 90-95.	1.5	14
67	High-quality AlN film grown on a nanosized concaveâ€“convex surface sapphire substrate by metalorganic vapor phase epitaxy. Applied Physics Letters, 2017, 111, .	3.3	23
68	Annealing of the sputtered AlN buffer layer on râ€plane sapphire and its effect on aâ€plane GaN crystalline quality. Physica Status Solidi (B): Basic Research, 2017, 254, 1600723.	1.5	8
69	High-performance solar-blind Al0.6Ga0.4N/Al0.5Ga0.5N MSM type photodetector. Applied Physics Letters, 2017, 111, .	3.3	39
70	GaInN-based tunnel junctions with graded layers. Applied Physics Express, 2016, 9, 081005.	2.4	27
71	Room-temperature continuous-wave operation of GaN-based vertical-cavity surface-emitting lasers with n-type conducting AlInN/GaN distributed Bragg reflectors. Applied Physics Express, 2016, 9, 102101.	2.4	78
72	Demonstration of electron beam excitation laser using a GaInN-based multiquantum well active layer. Applied Physics Express, 2016, 9, 101001.	2.4	1

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73	Relationship between misfit-dislocation formation and initial threading-dislocation density in GaInN/GaN heterostructures. Japanese Journal of Applied Physics, 2015, 54, 115501.	1.5	16
74	GaInNâ€based tunnel junctions with high InN mole fractions grown by MOVPE. Physica Status Solidi (B): Basic Research, 2015, 252, 1127-1131.	1.5	27
75	Control of crystallinity of GaN grown on sapphire substrate by metalorganic vapor phase epitaxy using in situ X-ray diffraction monitoring method. Journal of Crystal Growth, 2014, 401, 367-371.	1.5	60
76	Homoepitaxial growth of AlN layers on freestanding AlN substrate by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2014, 390, 46-50.	1.5	5
77	In situ X-ray diffraction monitoring of GaInN/GaN superlattice during organometalic vapor phase epitaxy growth. Journal of Crystal Growth, 2014, 393, 108-113.	1.5	8
78	Analysis of strain relaxation process in GaInN/GaN heterostructure by in situ Xâ€ray diffraction monitoring during metalorganic vaporâ€phase epitaxial growth. Physica Status Solidi - Rapid Research Letters, 2013, 7, 211-214.	2.4	20
79	GaInN-Based Tunnel Junctions in nâ€“pâ€“n Light Emitting Diodes. Japanese Journal of Applied Physics, 2013, 52, 08JH06.	1.5	51
80	Extremely Low-Resistivity and High-Carrier-Concentration Si-Doped Al_{0.05}Ga_{0.95}N. Applied Physics Express, 2013, 6, 121002.	2.4	27
81	Nitrideâ€based heteroâ€fieldâ€effectâ€transistorâ€type photosensors with extremely high photosensitivity. Physica Status Solidi - Rapid Research Letters, 2013, 7, 215-217.	2.4	4
82	Dislocation density dependence of stimulated emission characteristics in AlGaN/Al multiquantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1537-1540.	0.8	6
83	White light-emitting diode based on fluorescent SiC. Thin Solid Films, 2012, 522, 23-25.	1.8	21
84	Development of AlN/diamond heterojunction field effect transistors. Diamond and Related Materials, 2012, 24, 206-209.	3.9	31
85	MOVPE growth of nonpolar a-plane GaN with low oxygen contamination and specular surface on a freestanding GaN substrate. Journal of Crystal Growth, 2012, 351, 126-130.	1.5	0
86	In situ X-ray diffraction monitoring during metalorganic vapor phase epitaxy growth of low-temperature-GaN buffer layer. Journal of Crystal Growth, 2012, 361, 1-4.	1.5	7
87	Properties of nitrideâ€based photovoltaic cells under concentrated light illumination. Physica Status Solidi - Rapid Research Letters, 2012, 6, 145-147.	2.4	12
88	Injection efficiency in AlGaNâ€based UV laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2384-2386.	0.8	14
89	Reduction in threshold current density of 355 nm UV laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1564-1568.	0.8	13
90	GaInNâ€based solar cells using GaInN/GaInN superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2463-2465.	0.8	6

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91	Fabrication of Nonpolar a-Plane Nitride-Based Solar Cell on r-Plane Sapphire Substrate. Applied Physics Express, 2011, 4, 101001.	2.4	12
92	Improvement of Light Extraction Efficiency for AlGaN-Based Deep Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2011, 50, 122101.	1.5	52
93	Compensation effect of Mg-doped a- and c-plane GaN films grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 3131-3135.	1.5	30
94	Defects in highly Mgâ€doped AlN. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1299-1301.	1.8	1
95	Realization of extreme light extraction efficiency for mothâ€eye LEDs on SiC substrate using highâ€reflection electrode. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2180-2182.	0.8	11
96	Improved Efficiency of 255â€“280 nm AlGaN-Based Light-Emitting Diodes. Applied Physics Express, 2010, 3, 061004.	2.4	233
97	Strain Relaxation Mechanisms in AlGaN Epitaxy on AlN Templates. Applied Physics Express, 2010, 3, 111003.	2.4	20
98	Realization of Nitride-Based Solar Cell on Freestanding GaN Substrate. Applied Physics Express, 2010, 3, 111001.	2.4	52
99	Activation of Mg-Doped p-Type Al0.17Ga0.83N in Oxygen Ambient. Japanese Journal of Applied Physics, 2009, 48, 101002.	1.5	1
100	Highâ€performance UV emitter grown on highâ€crystallineâ€quality AlGaN underlying layer. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1199-1204.	1.8	41
101	Activation energy of Mg in a â€plane Ga_{1â€“x}In_x N (0 <) Tj ETQq1 1 0.784314 rgBT	1.5	3
102	Relaxation and recovery processes of AlxGa1â^'xN grown on AlN underlying layer. Journal of Crystal Growth, 2009, 311, 2850-2852.	1.5	12
103	Novel UV devices on high-quality AlGaN using grooved underlying layer. Journal of Crystal Growth, 2009, 311, 2860-2863.	1.5	55
104	One-sidewall-seeded epitaxial lateral overgrowth of a-plane GaN by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2009, 311, 2887-2890.	1.5	31
105	InGaN growth with various InN mole fractions on m-plane ZnO substrate by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2009, 311, 2929-2932.	1.5	2
106	Growth of thick GaInN on grooved (101Â¯1Â¯) GaN/(101Â¯2Â¯) 4H-SiC. Journal of Crystal Growth, 2009, 311, 2926-2928.	1.5	3
107	High-efficiency AlGaN-based UV light-emitting diode on laterally overgrown AlN. Journal of Crystal Growth, 2008, 310, 2326-2329.	1.5	54
108	Impact of high-temperature growth by metal-organic vapor phase epitaxy on microstructure of AlN on 6H-SiC substrates. Journal of Crystal Growth, 2008, 310, 2308-2313.	1.5	65

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109	Realization of low-dislocation-density, smooth surface, and thick GaInN films on m-plane GaN templates. Journal of Crystal Growth, 2008, 310, 3308-3312.	1.5	15
110	Control of p-type conduction in a-plane Ga1â^'xInxN (0<x<0.10) grown on r-plane sapphire substrate by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2008, 310, 4996-4998.	1.5	1
111	Control of stress and crystalline quality in GaInN films used for green emitters. Journal of Crystal Growth, 2008, 310, 4920-4922.	1.5	8
112	AlN and AlGaN by MOVPE for UV Light Emitting Devices. Materials Science Forum, 2008, 590, 175-210.	0.3	2
113	High hole concentration in Mg-doped a-plane Ga1â^'xInxNâ€^(<x<0.30) grown on r-plane sapphire substrate by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, .	3.3	14
114	Dislocations in AlN Epilayers Grown on Sapphire Substrate by High-Temperature Metal-Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 1458-1462.	1.5	90
115	Influence of High Temperature in the Growth of Low Dislocation Content AlN Bridge Layers on Patterned 6H-SiC Substrates by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, L307-L310.	1.5	45
116	Control of Threshold Voltage of Enhancement-Mode AlxGa1-xN/GaN Junction Heterostructure Field-Effect Transistors Using p-GaN Gate Contact. Japanese Journal of Applied Physics, 2007, 46, 115-118.	1.5	28
117	Realization of High-Crystalline-Quality Thick m-Plane GaInN Film on 6H-SiC Substrate by Epitaxial Lateral Overgrowth. Japanese Journal of Applied Physics, 2007, 46, L948.	1.5	14
118	Epitaxial lateral overgrowth of AlxGa1â^'xN (x>0.2) on sapphire and its application to UV-B-light-emitting devices. Journal of Crystal Growth, 2007, 298, 265-267.	1.5	18
119	Epitaxial lateral overgrowth of AlN on trench-patterned AlN layers. Journal of Crystal Growth, 2007, 298, 257-260.	1.5	104
120	Annihilation mechanism of threading dislocations in AlN grown by growth form modification method using V/III ratio. Journal of Crystal Growth, 2007, 300, 136-140.	1.5	66
121	Low-Leakage-Current Enhancement-Mode AlGaN/GaN Heterostructure Field-Effect Transistor Using p-Type Gate Contact. Japanese Journal of Applied Physics, 2006, 45, L319-L321.	1.5	30
122	High On/Off Ratio in Enhancement-Mode AlxGa1-xN/GaN Junction Heterostructure Field-Effect Transistors with P-Type GaN Gate Contact. Japanese Journal of Applied Physics, 2006, 45, L1048-L1050.	1.5	25
123	X-ray diffraction reciprocal lattice space mapping ofa-plane AlGaN on GaN. Physica Status Solidi (B): Basic Research, 2006, 243, 1524-1528.	1.5	12
124	Thermodynamic Aspects of Growth of AlGaN by High-Temperature Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 2502-2504.	1.5	26
125	Anisotropically Biaxial Strain ina-Plane AlGaN on GaN Grown onr-Plane Sapphire. Japanese Journal of Applied Physics, 2006, 45, 2509-2513.	1.5	22
126	Details of the improvement of crystalline quality of a-plane GaN using one-step lateral growth. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0

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127	Fabrication of high-performance photodetector based on AlGaN/GaN hetero-field-effect transistors with p-GaN gate. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
128	High-Temperature Metal-Organic Vapor Phase Epitaxial Growth of AlN on Sapphire by Multi Transition Growth Mode Method Varying V/III Ratio. Japanese Journal of Applied Physics, 2006, 45, 8639-8643.	1.5	101
129	Flat (11ar20) GaN Thin Film on Precisely Offset-Controlled (1ar102) Sapphire Substrate. Japanese Journal of Applied Physics, 2005, 44, 7418-7420.	1.5	44
130	Control of p-Type Conduction in a-Plane GaN Grown on Sapphire r-Plane Substrate. Japanese Journal of Applied Physics, 2005, 44, L1516-L1518.	1.5	44
131	Impact of H2-Preannealing of the Sapphire Substrate on the Crystallinity of Low-Temperature-Deposited AlN Buffer Layer. Japanese Journal of Applied Physics, 2005, 44, 3913-3917.	1.5	5
132	High-Efficiency Nitride-Based Light-Emitting Diodes with Moth-Eye Structure. Japanese Journal of Applied Physics, 2005, 44, 7414-7417.	1.5	39
133	Moth-Eye Light-Emitting Diodes. Materials Research Society Symposia Proceedings, 2004, 831, 19.	0.1	1
134	Study on the Seeded Growth of AlN Bulk Crystals by Sublimation. Japanese Journal of Applied Physics, 2004, 43, 7448-7453.	1.5	7
135	350.9 nm UV Laser Diode Grown on Low-Dislocation-Density AlGaN. Japanese Journal of Applied Physics, 2004, 43, L499-L500.	1.5	151
136	Laser diode of 350.9nm wavelength grown on sapphire substrate by MOVPE. Journal of Crystal Growth, 2004, 272, 270-273.	1.5	33
137	High-quality Al0.12Ga0.88N film with low dislocation density grown on facet-controlled Al0.12Ga0.88N by MOVPE. Journal of Crystal Growth, 2004, 272, 377-380.	1.5	11
138	High-Power UV-Light-Emitting Diode on Sapphire. Japanese Journal of Applied Physics, 2003, 42, 400-403.	1.5	29
139	In-plane GaN/AlGaN heterostructure fabricated by selective mass transport planar technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 139-142.	3.5	9
140	Relaxation of misfit-induced stress in nitride-based heterostructures. Journal of Crystal Growth, 2002, 237-239, 947-950.	1.5	9
141	Low-temperature-deposited AlGaN interlayer for improvement of AlGaN/GaN heterostructure. Journal of Crystal Growth, 2001, 223, 83-91.	1.5	82
142	Fracture of AlxGa1-xN/GaN Heterostructure -- Compositional and Impurity Dependence --. Japanese Journal of Applied Physics, 2001, 40, L195-L197.	1.5	33
143	Photoresponse and Defect Levels of AlGaN/GaN Heterobipolar Phototransistor Grown on Low-Temperature AlN Interlayer. Japanese Journal of Applied Physics, 2001, 40, L498-L501.	1.5	18
144	Realization of crack-free and high-quality thick AlxGa1â^'xN for UV optoelectronics using low-temperature interlayer. Applied Surface Science, 2000, 159-160, 405-413.	6.1	56

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145	Electrical Conductivity of Low-Temperature-Deposited Al0.1Ga0.9N Interlayer. Japanese Journal of Applied Physics, 2000, 39, 6493-6495.	1.5	1
146	Performance of GaN-Based Semiconductor Laser with Spectral Broadening due to Compositional Inhomogeneity in GaInN Active Layer. Japanese Journal of Applied Physics, 2000, 39, 390-392.	1.5	5
147	Solar-Blind UV Photodetectors Based on GaN/AlGaN p-i-n Photodiodes. Japanese Journal of Applied Physics, 2000, 39, L387-L389.	1.5	108
148	Microscopic Investigation of Al0.43Ga0.57N on Sapphire. Japanese Journal of Applied Physics, 1999, 38, L1515-L1518.	1.5	33
149	Low-Intensity Ultraviolet Photodetectors Based on AlGaN. Japanese Journal of Applied Physics, 1999, 38, L487-L489.	1.5	45
150	Reduction of Etch Pit Density in Organometallic Vapor Phase Epitaxy-Grown GaN on Sapphire by Insertion of a Low-Temperature-Deposited Buffer Layer between High-Temperature-Grown GaN. Japanese Journal of Applied Physics, 1998, 37, L316-L318.	1.5	184
151	Stress and Defect Control in GaN Using Low Temperature Interlayers. Japanese Journal of Applied Physics, 1998, 37, L1540-L1542.	1.5	150
152	Study on N and B Doping by Closed Sublimation Growth Using Separated Ta Crucible. Materials Science Forum, 0, 963, 34-37.	0.3	1
153	Photoluminescence Characterization of Fluorescent Sic with High Boron and Nitrogen Concentrations. Materials Science Forum, 0, 1004, 265-271.	0.3	4
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